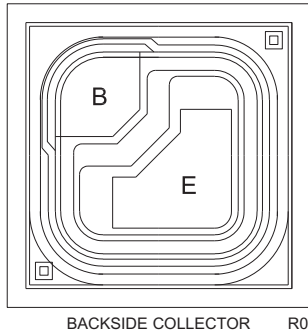


CP788X-BCW70

PNP - General Purpose Transistor Die

The CP788X-BCW70 is a silicon PNP transistor designed for general purpose applications.



MECHANICAL SPECIFICATIONS:

Die Size	13.7 x 13.7 MILS
Die Thickness	5.9 MILS
Base Bonding Pad Size	4.0 x 4.0 MILS
Emitter Bonding Pad Size	5.5 x 5.5 MILS
Top Side Metalization	Al-Si – 17,000Å
Back Side Metalization	Au – 9,000Å
Scribe Alley Width	1.8 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	91,469

MAXIMUM RATINGS: (T_A=25°C)

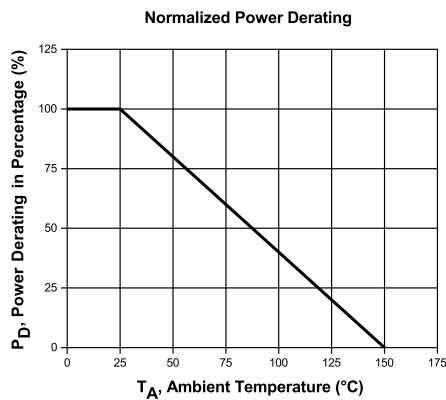
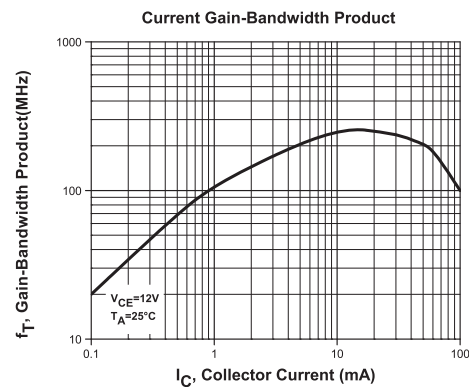
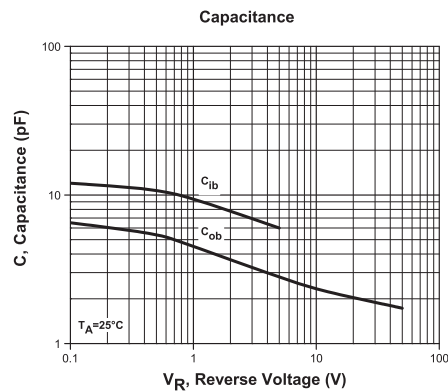
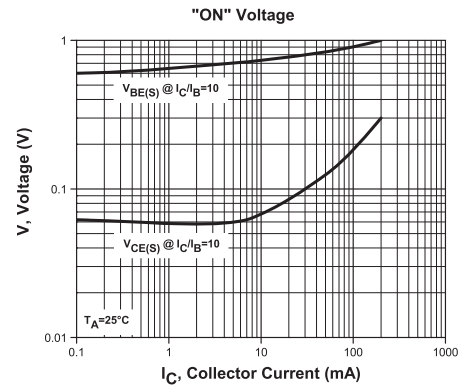
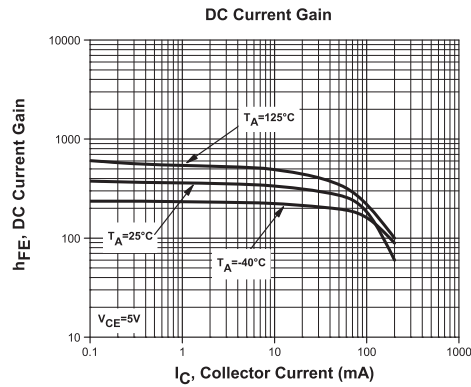
	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	I _C	100	mA
Peak Collector Current	I _{CM}	200	mA
Peak Base Current	I _{BM}	200	mA
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} =20V			100	nA
I _{EBO}	V _{EB} =5.0V			100	nA
V _{CE(SAT)}	I _C =10mA, I _B =0.5mA			0.30	V
V _{BE(SAT)}	I _C =10mA, I _B =0.5mA		0.72		V
V _{BE(SAT)}	I _C =50mA, I _B =2.5mA		0.81		V
V _{BE(ON)}	V _{CE} =5.0V, I _C =2.0mA	0.60		0.75	V
h _{FE}	V _{CE} =5.0V, I _C =10μA		150		
h _{FE}	V _{CE} =5.0V, I _C =2.0mA	215		500	
f _T	V _{CE} =5.0V, I _C =10mA, f=100MHz	100			MHz
C _c	V _{CB} =10V, I _E =0, f=1.0MHz		4.5		pF
NF	V _{CE} =5.0V, I _C =200μA, R _S =2.0kΩ, f=1.0kHz, BW=200Hz			10	dB

CP788X-BCW70

Typical Electrical Characteristics



BARE DIE PACKING OPTIONS



BARE DIE IN TRAY (WAFFLE) PACK

CT: Singulated die in tray (waffle) pack.
(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes).
(example: CP211-PART NUMBER-CM)



UNSAWN WAFER

WN: Full wafer, unsawn, 100% tested with reject die inked.
(example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring,
100% tested with reject die inked.
(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications:
www.centrasemi.com/bdspecs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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